

Radar Pulsed Power Transistor 65W, 2.7-2.9 GHz, 100µs Pulse, 10% Duty

M/A-COM Products Released, 29 Jun 07

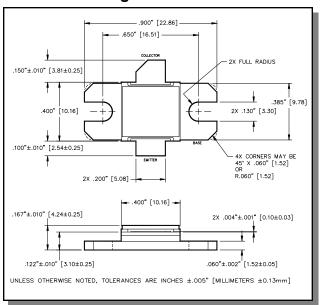
Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- · Hermetic metal/ceramic package
- RoHS compliant

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	65	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I _C	8.0	Α
Power Dissipation @ +25°C	P _{TOT}	330	W
Storage Temperature	T _{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 50mA		BV _{CES}	65	-	V
Collector-Emitter Leakage Current	V _{CE} = 36V		I _{CES}	-	7.5	mA
Thermal Resistance	Vcc = 36V, Pout = 65W	F = 2.7, 2.8, 2.9 GHz	R _{TH(JC)}	-	0.45	°C/W
Input Power	Vcc = 36V, Pout = 65W	F = 2.7, 2.8, 2.9 GHz	P _{IN}	-	9.0	W
Power Gain	Vcc = 36V, Pout = 65W	F = 2.7, 2.8, 2.9 GHz	G _P	8.5	=	dB
Collector Efficiency	Vcc = 36V, Pout = 65W	F = 2.7, 2.8, 2.9 GHz	ης	40	i	%
Input Return Loss	Vcc = 36V, Pout = 65W	F = 2.7, 2.8, 2.9 GHz	RL	-	-9	dB
Load Mismatch Tolerance	Vcc = 36V, Pout = 65W	F = 2.7, 2.8, 2.9 GHz	VSWR-T	-	2:1	-
Load Mismatch Stability	Vcc = 36V, Pout = 65W	F = 2.7, 2.8, 2.9 GHz	VSWR-S	-	1.5:1	-

Commitment to produce in volume is not qua

- North America Tel: 800.366.2266 / Fax: 978.366.2266
- **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300
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 Visit www.macomtech.com for additional data sheets and product information.

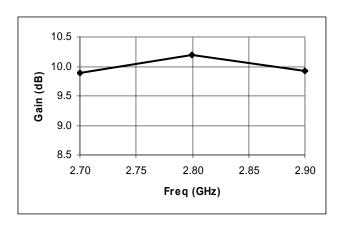


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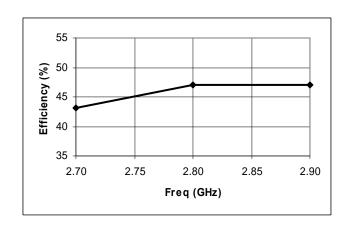
Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (2:1)
2.7	6.7	65	9.88	4.20	43.1	-15.5	S	Р
2.8	6.2	65	10.20	3.84	47.0	-17.9	S	Р
2.9	6.6	65	9.93	3.83	47.1	-12.4	S	Р

Gain vs. Frequency



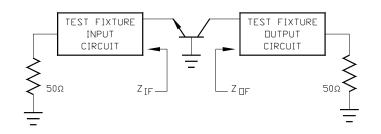
Collector Efficiency vs. Frequency



RF Test Fixture Impedance

typical. Mechanical outline has been fixed. Engineering samples Commitment to produce in volume is not guaranteed.

F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)		
2.7	7.8 - j8.3	9.3 - j8.9		
2.8	7.3 - j6.7	9.0 - j8.4		
2.9	7.2 - j5.0	8.6 - j8.0		



PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are

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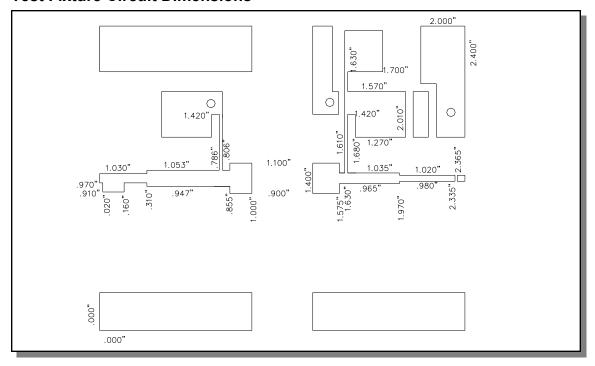
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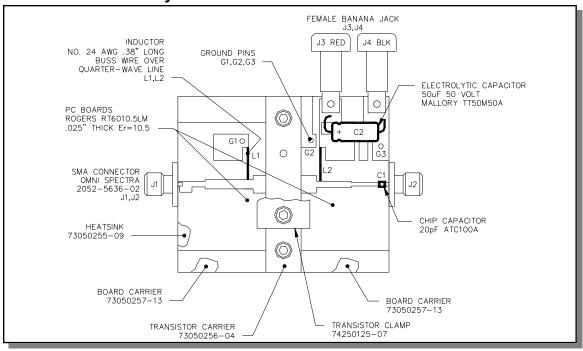
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Test Fixture Circuit Dimensions



Test Fixture Assembly

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